

Abstract of the Disclosure:

An integrated magnetoresisitive semiconductor memory configuration has MRAM memory cells located at crossover points of selection lines that are embedded in different, 5 mutually separate line planes. A read/write current can be impressed in respective selection lines for writing to each MRAM memory cell and for reading an information item written therein. In this magnetoresistive semiconductor memory configuration, selection lines that serve for reading a cell 10 information item are in each case located in separate first and second line planes in direct contact with the memory cells. A third and a fourth line plane are spatially separated and electrically isolated from the first and second line planes and are occupied by write selection lines for writing a 15 cell information item.

MPW/nt